

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A pattern forming method comprising steps of:

forming a thin film on a surface;

positioning the surface and ~~[[,]]~~ a first nozzle ~~and a second nozzle, the first and the second nozzles being integrated,~~ so that the first nozzle is ~~and the second nozzle are~~ in a region located above a selected portion of the thin film;

irradiating the selected portion of the ~~liquid-repellent~~ thin film with ~~[[a]]~~ gas plasma ~~of a gas irradiated~~ ~~originating~~ from the first nozzle to selectively provide affinity for ~~[[the]]~~ a liquid composition to the selected portion, after the step of positioning the ~~integrated~~ first nozzle ~~and the integrated second nozzle;~~ and

applying ~~[[a]]~~ the liquid composition to the selected portion by discharging a drop from ~~[[the]]~~ a second nozzle by drop discharging method, after having irradiated the selected portion with ~~[[the]]~~ plasma gas,

forming a pattern by repeating said steps of positioning, irradiating, and applying,

etching the thin film by plasma etching using gas plasma irradiated ~~sprayed~~ by an array of nozzles over an area including the selected portion of the thin film and the pattern, and using the pattern as mask;

wherein a larger quantity of gas plasma is irradiated ~~sprayed~~ over regions where the thin film is exposed than over the pattern varies according to the pattern.

2. (Canceled)

3. (Previously Presented) A pattern forming method according to claim 1, wherein the liquid composition comprises at least one selected from the group consisting of a conductive material, a resist material, a polymer material and a light emitting material.

4. (Currently Amended) A pattern forming method according to claim 1, wherein the liquid-repellent thin film is selected from the group consisting of a semiconductor film, a conductive film and a polymer film.

5. (Canceled)

6. (Currently amended) A pattern forming method according to claim 1, wherein the irradiation with ~~[[the]]~~ gas plasma is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.

7-22. (Canceled)

23. (Currently amended) A pattern forming method comprising steps of:
positioning a surface~~[[,]]~~ and a first nozzle ~~and a second nozzle, the first and the second nozzles being integrated,~~ so that the first nozzle ~~and the second nozzle are~~ is in a region located above a selected portion of the surface;

irradiating the selected portion of the surface with ~~[[a]]~~ gas plasma ~~of a gas irradiated~~

~~originating from the first nozzle to selectively provide affinity for a liquid composition having electrical conductivity, after the step of positioning the integrated first nozzle and the integrated second nozzle;~~

forming a conductive film by applying the liquid composition having electrical conductivity to the selected portion by discharging a drop from ~~[[the]]~~ a second nozzle by drop discharging method, after having irradiated the selected portion with ~~[[the]]~~ gas plasma;

forming a mask pattern made of a resist composition over a part of the selected portion; and
etching the conductive film selectively according to the mask pattern to form a conductive pattern by plasma etching using gas plasma irradiated over an area including the selected portion of the conductive film and the mask pattern,

wherein a larger quantity of gas plasma is irradiated ~~sprayed~~ by an array of nozzles for the plasma etching ~~varies according to~~ over regions where the conductive film is exposed than over the mask pattern; and

wherein a predetermined wiring pattern is formed by repeating said steps of positioning, irradiating, applying, mask pattern forming, and etching.

24. (Currently amended) A pattern forming method according to claim 23, wherein ~~[[the]]~~ gas to form gas plasma is selected from the group consisting of He, Ne, Ar, Kr, Xe, oxygen, nitrogen and a combination thereof.

25. (Previously Presented) A pattern forming method according to claim 23 wherein the mask pattern is formed by selectively applying the resist composition to the conductive pattern through a

nozzle.

26-28. (Canceled)

29. (Previously Presented) A pattern forming method according to claim 1, wherein the application of the liquid composition is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.

30. (Canceled)

31. (Currently Amended) A pattern forming method according to claim 23, wherein the etching is performed by locally discharging gas plasma from plural nozzles ~~plasma-discharge ports~~.

32. (Canceled)

33. (New) A pattern forming method according to claim 1, wherein the first nozzle and the second nozzle are integrated.

34. (New) A pattern forming method according to claim 23, wherein the first nozzle and the second nozzle are integrated.